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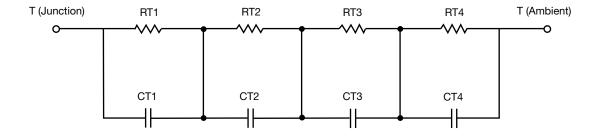
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK	ALUES FOR TANK CONFIGURATION				
	THERMAL RES	ISTANCE (°C/W)			
Junction to	Ambient	Case	Foot		
RT1	N/A	125.8120m	N/A		
RT2	N/A	144.0086m	N/A		
RT3	N/A	135.6198m	N/A		
RT4	N/A	146.4684m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	N/A	169.0479m	N/A		
CT2	N/A	146.9823m	N/A		
CT3	N/A	157.2068m	N/A		
CT4	N/A	143.6119m	N/A		

Note

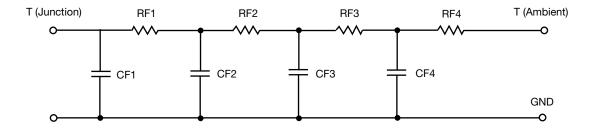
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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R-C THERMAL MODEL FOR FILTER CONFIGURATION



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	N/A	419.7078m	N/A		
RF2	N/A	109.8864m	N/A		
RF3	N/A	20.0065m	N/A		
RF4	N/A	3.1381m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	N/A	36.0664m	N/A		
CF2	N/A	39.9261m	N/A		
CF3	N/A	38.8906m	N/A		
CF4	N/A	13.7796u	N/A		

Note

• n/a indicates not applicable





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